

Abstract of the Disclosure

The present invention includes a method for preventing distortion in semiconductor fabrication. The method comprises providing a substrate comprising a film comprising silicon nitride. The substrate is treated in a vacuum of about 3.0-6.5 Torr in an atmosphere comprising oxygen plasma wherein the oxygen plasma flow rate is at least about 300 sccm oxygen. A resist is applied to the treated substrate and the resist is patterned over the treated substrate.

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00258762-030400

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